

# **CPH6519**

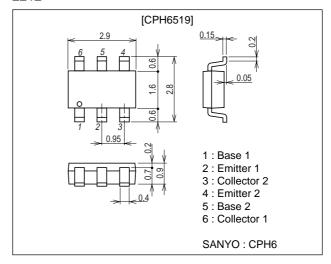
# Low-Frequency General-Purpose Amplifier, Driver Applications

### **Features**

- Composite type with 2 transistors contained in the CPH package currently in use, improving the mounting efficiency greatly.
- The CPH6519 is formed with two chips, being equivalent to the 2SC3689, placed in one package.
- · Adoption of FBET process.
- High DC current gain (hFE=800 to 3200).
- · High VEBO (VEBO≥15V).
- · Excellent in thermal equilibrium and pair capability.

## **Package Dimensions**

unit : mm 2212



# **Specifications**

### Absolute Maximum Ratings at Ta=25°C

| Parameter                    | Symbol | Conditions | Ratings     | Unit |
|------------------------------|--------|------------|-------------|------|
| Collector-to-Base Voltage    | VCBO   |            | 60          | V    |
| Collector-to-Emitter Voltage | VCEO   |            | 50          | V    |
| Emitter-to-Base Voltage      | VEBO   |            | 15          | V    |
| Collector Current            | IC     |            | 100         | mA   |
| Collector Current (Pulse)    | ICP    |            | 200         | mA   |
| Base Current                 | IB     |            | 20          | mA   |
| Collector Dissipation        | PC     | 1unit      | 350         | mW   |
| Total Dissipation            | PT     |            | 500         | mW   |
| Junction Temperature         | Tj     |            | 150         | °C   |
| Storage Temperature          | Tstg   |            | -55 to +150 | °C   |

#### Electrical Characteristics at Ta=25°C

| Parameter                | Symbol               | Conditions                                | Ratings |      |      | Unit |
|--------------------------|----------------------|---|---------|------|------|------|
|                          |                      |   | min     | typ  | max  | Oill |
| Collector Cutoff Current | ІСВО                 | V <sub>CB</sub> =40V, I <sub>E</sub> =0   |         |      | 0.1  | μΑ   |
| Emitter Cutoff Current   | IEBO                 | V <sub>EB</sub> =10V, I <sub>C</sub> =0   |         |      | 0.1  | μΑ   |
| DC Current Gain          | hFE                  | V <sub>CE</sub> =5V, I <sub>C</sub> =10mA | 800     | 1500 | 3200 |      |
| DC Current Gain Ratio    | hFE(small/<br>large) | VCE=5V, IC=10mA                           | 0.8     | 0.98 |      |      |

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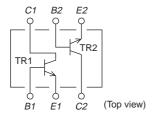
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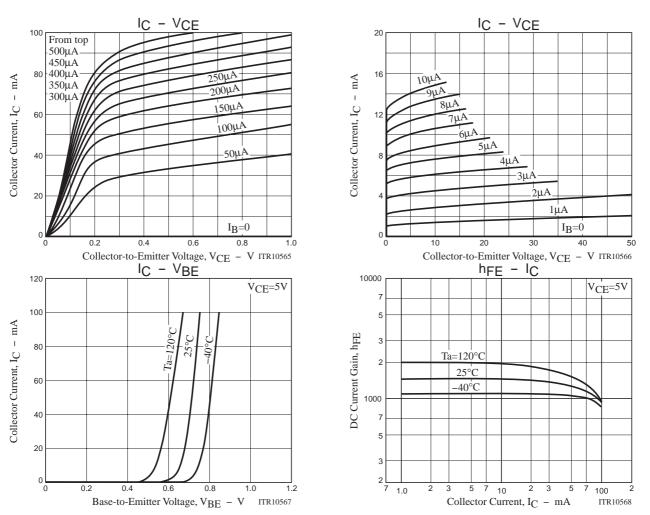
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| Parameter                               | Symbol                | Conditions                                 | Ratings |     |     | Unit  |
|---|-----------------------|--|---------|-----|-----|-------|
|   |                       |  | min     | typ | max | Offit |
| Gain-Bandwidth Product                  | fT                    | V <sub>CE</sub> =10V, I <sub>C</sub> =10mA |         | 200 |     | MHz   |
| Output Capacitance                      | Cob                   | V <sub>CB</sub> =10V, f=1MHz               |         | 1.5 |     | pF    |
| Collector-to-Emitter Saturation Voltage | VCE(sat)              | IC=50mA, IB=1mA                            |         | 0.1 | 0.5 | V     |
| Base-to-Emitter Saturation Voltage      | V <sub>BE</sub> (sat) | IC=50mA, IB=1mA                            |         | 0.8 | 1.1 | ٧     |
| Collector-to-Base Breakdown Voltage     | V(BR)CBO              | I <sub>C</sub> =10μA, I <sub>E</sub> =0    | 60      |     |     | V     |
| Collector-to-Emitter Breakdown Voltage  | V(BR)CEO              | IC=1mA, RBE=∞                              | 50      |     |     | V     |
| Emitter-to-Base Breakdown Voltage       | V(BR)EBO              | I <sub>E</sub> =10μA, I <sub>C</sub> =0    | 15      |     |     | V     |

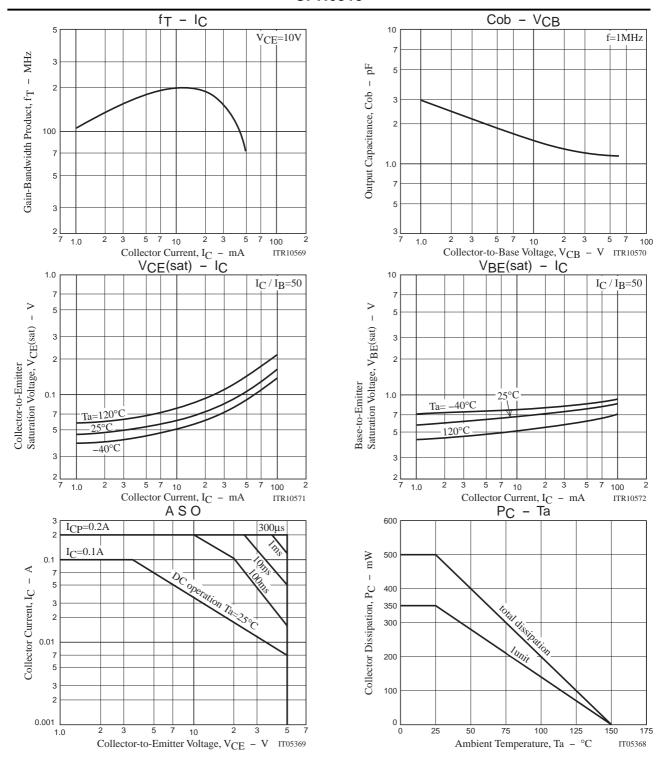
Note: The specifications shown above are for each individual transistor.

## **Electrical Connection**





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